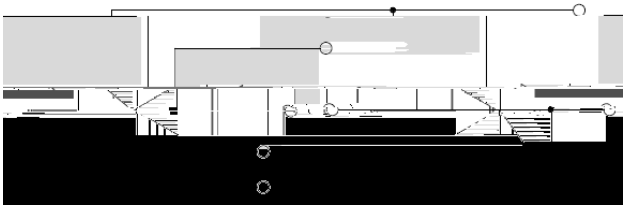
JMT110KT18T1

Thyristor Module

Features

- Half-bridge SCR configuration integrated in a single package
- High-thermal-conductivity DBC insulati1 (t)6.3u 0 Tw 3.391 0 Td (-)Tj 0.013 (i)6.3 (1 (t)6.3u 0 Tw 3.391 1 (nt)6o013 Tc -0

Parameter	Value	Unit
V_{RRM}	1800	V
$I_{T(AV)}$(@ T_C = 85)	110	A
I_{TSM}(@ t_P = 10ms)	2250	A
V_T(Max)	1.80	V



	Conditions	Symbol	Values	Unit
Repetitive peak off-state voltage	Tvj = 25°C	V_{DRM}	1800	V
Repetitive peak reverse voltage	Tvj = 25°C	V_{RRM}	1800	V0
Non-repetitive peak off-state voltage	Tvj = 25°C	V_{DSM}	1900	V
Non-repetitive peak reverse voltage	Tvj = 25°C	V_{RSM}	1900	V
Average forward current	T_C = 85°C	$I_{T(AV)}$	110	A 3ii 3-4.7 (3-4.7en( )

Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak forward voltage	I_T=330A, t_P=380μs	V_T			1.80	V
Repetitive peak off-state current	V_D = V_{DRM},T_{vj} = 25	I_{DRM}			100	μA
	V_D = V_{DRM},T_{vj} = 125				40	mA
Reverse leakage current	V_R = V_{RRM},T_{vj} = 25	I_{RRM}			100	μA
	V_R = V_{RRM},T_{vj} = 125				40	mA
Threshold voltage	For power loss calculation only T_{vj} = 125 ,	V_{TO}			0.88	V
Dynamic resistance	T_{vj} = 125 ,	r_T			2.4	mΩ
Triggering gate current	V_D=12V R_L=30Ω	I_{GT}	20		120	mA
Holding current	I_T=1A	I_H			250	mA
Latching current	I_G=1.2 I_{GT}	I_L			300	mA
Critical rate of rise of voltage	V_D=2/3V_{DRM} Tvj=125 Gate Open	dv/dt	1000			V/μs

Ordering Information

Device	Marking	Package	Weight	Inner Box	Pre Carton
JMT110KT18T1	JMT110KT18T1	T1	100g ± 5/PCS	10 PCS	120 PCS

Typical Electrical & Thermal Characteristics

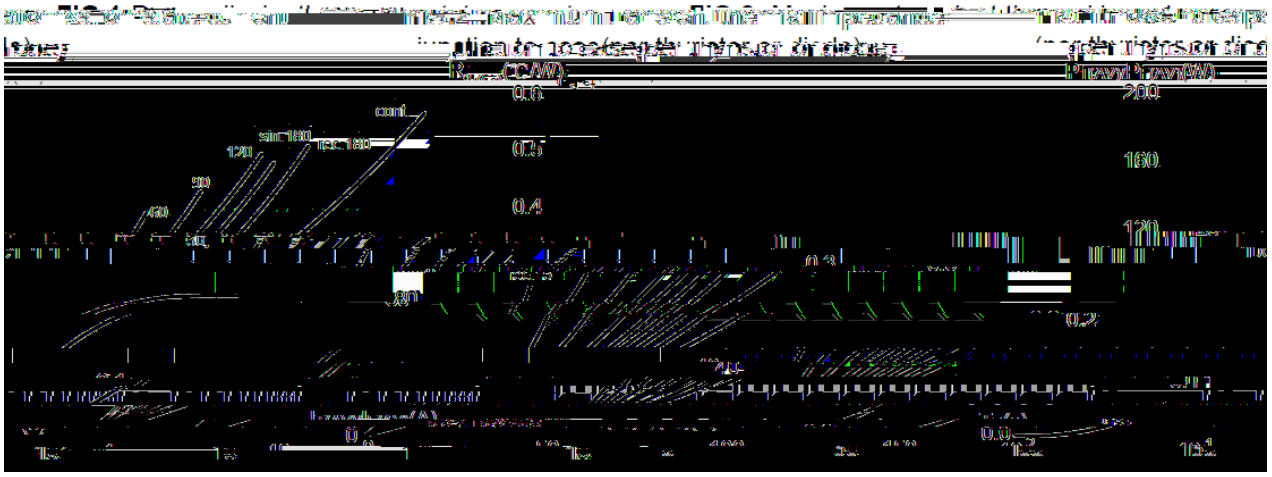
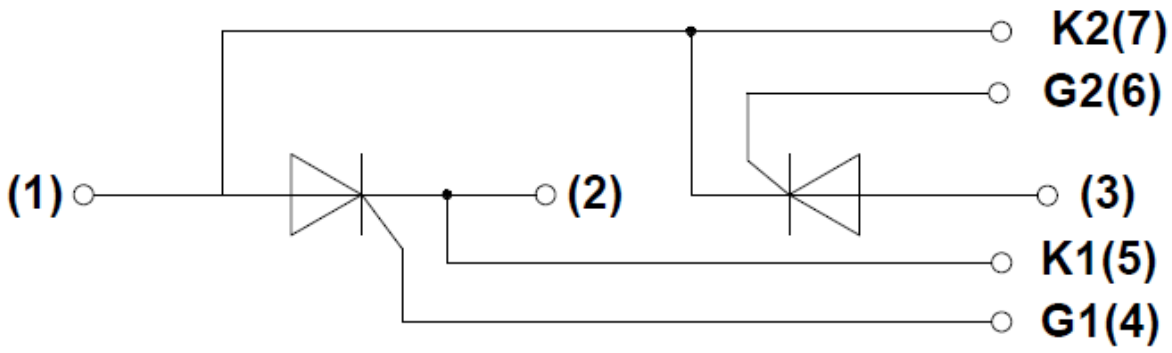


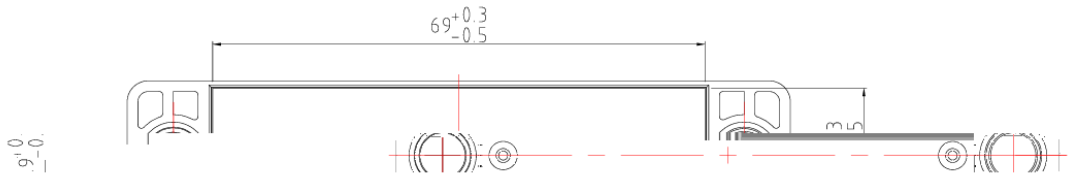
FIG.3:Forward characteristics

FIG.4: Relative variations of gate trigger current, holding

Circuit Diagram



Package Outlines (mm)



Unit of measurement: mm

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